

A cross-sectional view of a semiconductor device 300. The device includes a substrate 102 with a top surface 103 and a bottom surface 110. A layer 702 is formed on the top surface 103. A layer 704 is formed on the top surface 103, and a layer 706 is formed on the top surface 103. A layer 302 is formed on the top surface 103, and a layer 304 is formed on the top surface 103. A layer 306 is formed on the top surface 103. A layer 300 is formed on the top surface 103.

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